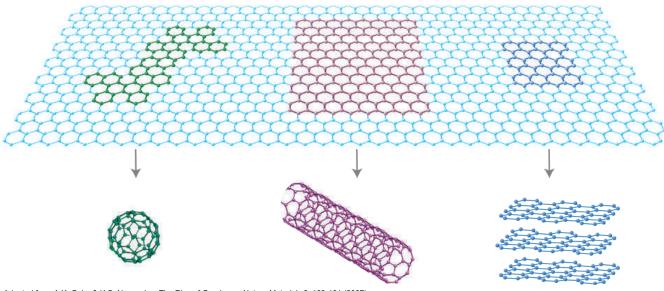
## Face to Face GRAPHENE Transfer

Alex An, Srivatsan Balakrishnan, Yang Bai

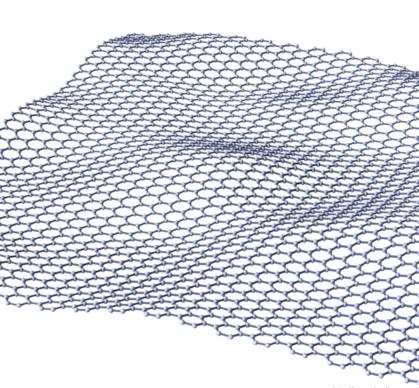
L. Gao et al. Face-to-face transfer of wafer-scale graphene films. Nature **505**, 190-194 (2014).



Adapted from A.K. Geim & K.S. Novoselov, The Rise of Graphene. *Nature Materials* **6**, 183-191 (2007).

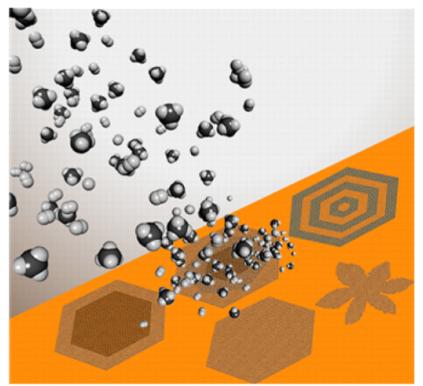
#### Outline

- Why care about graphene transfer?
- Conventional transfer techniques
- A better method: face to face transfer
- Faster etching than float transfer
- Improved properties of face to face transferred graphene
- Conclusion
- Evaluation
- Praise from critics



## Why is Transfer Useful?

- Graphene can be grown on Copper substrates by chemical vapor deposition (CVD)
- Many applications require graphene on other substrates like Silicon
- Transfer between the substrates is necessary
- Better transfer techniques can improve quality of graphene



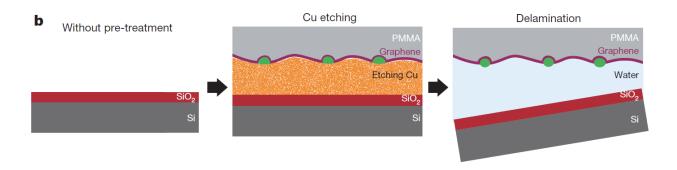
Z.Yan, Z.Peng, & J.M. Tour, Chemical Vapor Deposition of Graphene Single Crystals. Acc. Chem. Res. 47, 1327-1337 (2014)

## Conventional Techniques for Graphene Transfer

- Dry Transfer
  - Infamous Scotch Tape
  - High quality, but small pieces
- Wet Transfer
  - "Float transfer" separates the growth from the transfer
  - Low quality, but large pieces



http://graphene-supermarket.com



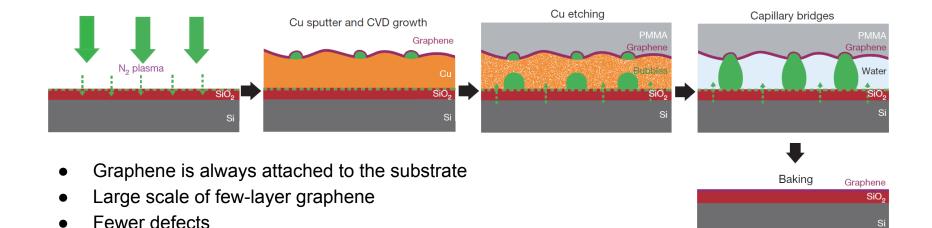
## Nature Provides the Motivation for Face to Face Transfer



http://avaxnews.net/pictures/61162

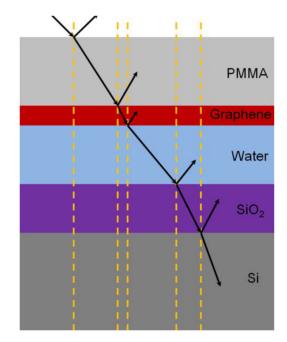
## The Face to Face Transfer Technique

Faster fabrication

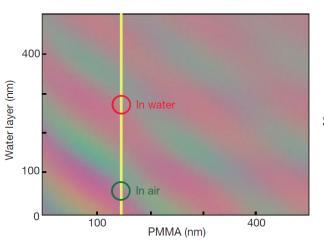


Amenable to batch processing in a semiconductor production line

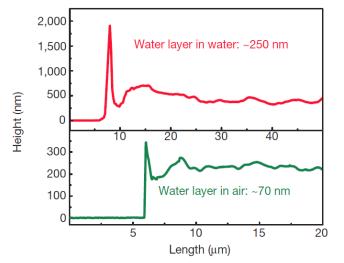
#### **Detecting the Water Layer**



Refracted and reflected paths in sample

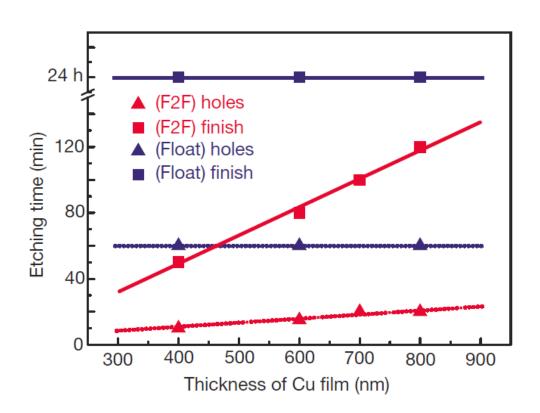


Simulated color change

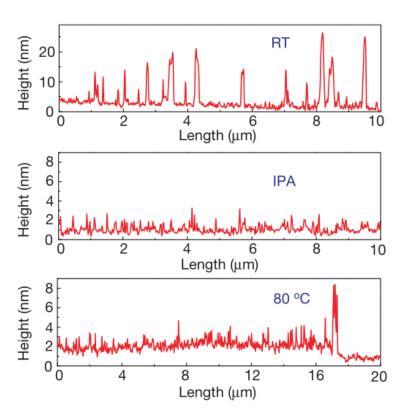


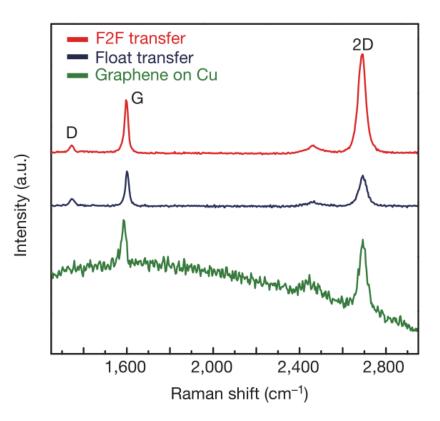
AFM scans of water layer thickness

## Face to Face Transfer Offers Faster Etching Times



## Face to Face Transfer Maintains Structure of Graphene

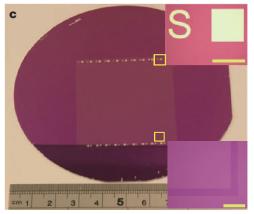


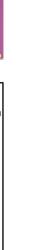


AFM height profiles showing uniformity of fabricated graphene

Raman spectra showing long range order

#### Transferred Graphene Exhibits Good Electrical Properties

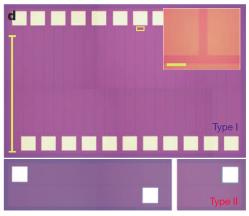


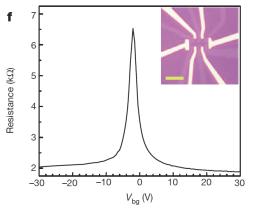


 $V_{\rm DS} = 0.2 \, {\rm V}$ 

Type IType II

42.5





Carrier mobility: 3800 cm<sup>2</sup> V<sup>-1</sup> s<sup>-1</sup>

Conductivity: 4000 S cm<sup>-1</sup>

e

Resistance (M $\Omega$ )

2.5 7.5 12.5 17.5

12.5

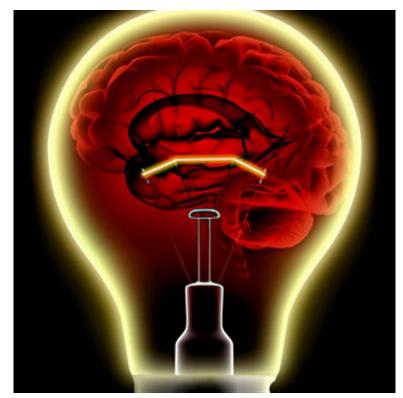
22.5

Ribbon length (mm)

32.5

#### Conclusion

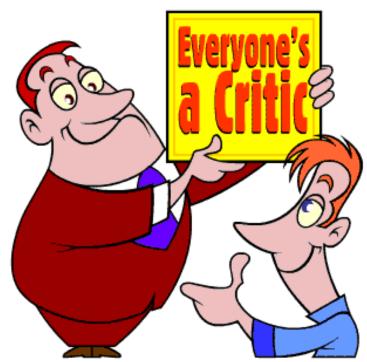
- Gas bubbles can effectively decrease transfer defects.
- Face-to-face transfer is compatible with any size and shape of substrate
- Face-to-face transfer can accomplish both the growth and transfer steps on one wafer
- Face-to-face nature of the transfer eliminates the manual fishing of floating Graphene.
- Graphene transferred by face-to-face is structurally better than by float transfer and offers good carrier mobility.



http://medicine.yale.edu/lab/mccormick/Images/full694\_167672ppt3slide15a.jpg

#### **Evaluation**

- The water layer and carrier mobility graphs are presented without much context.
- Constant etching time for float transfer needs explanation.
- Treatment of the substrate with the Nitrogen plasma for bubble seeding is an novel idea.
- This is a potentially breakthrough attempt at automated production of graphene.



http://wegotthiscovered.com/tv/couch-critics/

# Praise from Critics

#### Cited **32** times since November 2013.

- "A potential breakthrough"<sup>1</sup>
- "Has brought great promise for CVD-grown graphene films in industrially scalable devices"<sup>2</sup>
- "The greatest advantage of the technique is that it is automatically compatible and industrially scalable"
- "Excellent progress toward synthesizing defects free graphene sheets"
- "The face to face transfer method has demonstrated the transfer of 8 inches wafer-scale graphene onto silicon substrate successfully"

- [1] J.A. Torres, R.B. Kaner, Nature Materials (2014).
- [2] H.P. Cong, J.F. Chen, S.H. Yu, Chem. Soc. Rev. (2014).
- [3] X. Wan, K. Chen, J. Xu, Small (2014).
- [4] M.A.N. Dewapriya, R.K.N.D. Rajapakse, *Journal of Applied Mechanics*,(2014)
- [5] H. Tian, H.Y. Chen, T.L. Ren et al., Nano Letters, (2014)